![SGS-THOMSON MICROELECTRONICS logo]

M54HC273
M74HC273

OCTAL D TYPE FLIP FLOP WITH CLEAR

- HIGH SPEED
  f_{MAX} = 67 MHz (TYP.) AT V_{CC} = 5 V
- LOW POWER DISSIPATION
  I_{CC} = 4 μA (MAX.) AT T_A = 25 °C
- HIGH NOISE IMMUNITY
  V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|IOH|$ = I_{OL} = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  t_{PLH} = t_{PHL}
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2 V TO 6 V
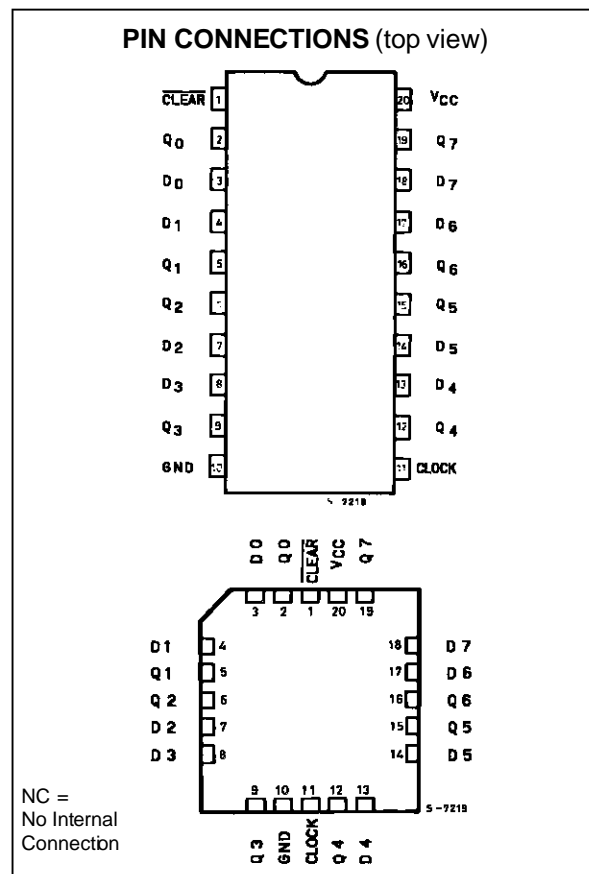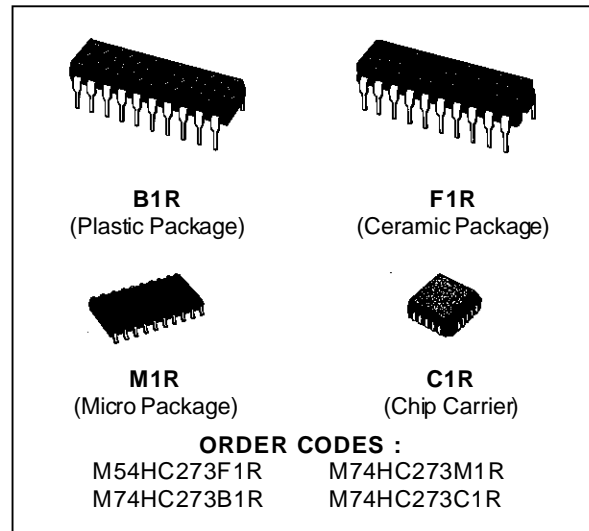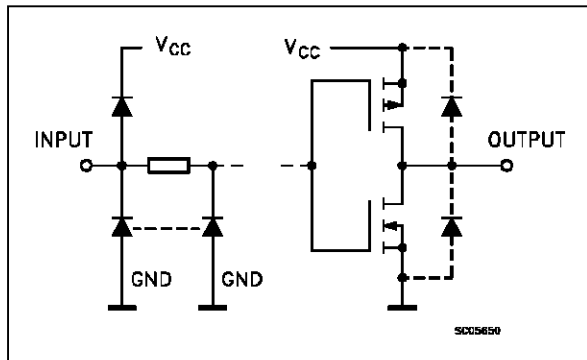- PIN AND FUNCTION COMPATIBLE WITH 54/74LS273

DESCRIPTION

The M54/74HC273 is a high speed CMOS OCTAL D-TYPE FLIP FLOP WITH CLEAR fabricated in silicon gate C^2MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption.

Information signals applied to D inputs are transferred to the Q outputs on the positive-going edge of the clock pulse.

When the $\overline{CLEAR}$ input is held low, the Q output are in the low logic level independent of the other inputs.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT

B1R
(Plastic Package)

F1R
(Ceramic Package)

M1R
(Micro Package)

C1R
(Chip Carrier)

ORDER CODES :
M54HC273F1R   M74HC273M1R
M74HC273B1R   M74HC273C1R

PIN CONNECTIONS (top view)

$\overline{CLEAR}$ 1	20	V_{CC}
Q_0 2	19	Q_7
D_0 3	18	D_7
D_1 4	17	D_6
Q_1 5	16	Q_6
Q_2 6	15	Q_5
D_2 7	14	D_5
D_3 8	13	D_4
Q_3 9	12	Q_4
GND 10	11	CLOCK

NC =
No Internal
Connection

PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	$\overline{\text{CLEAR}}$	Master Reset Input (Active LOW)
2, 5, 6, 9, 12, 15, 16, 19	Q0 to Q7	Flip Flop Outputs
3, 4, 7, 8, 13, 14, 17, 18	D0 to D7	Data Inputs
11	CLOCK	Clock Input (LOW to HIGH, Edge Triggered)
10	GND	Ground (0V)
20	V_{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL
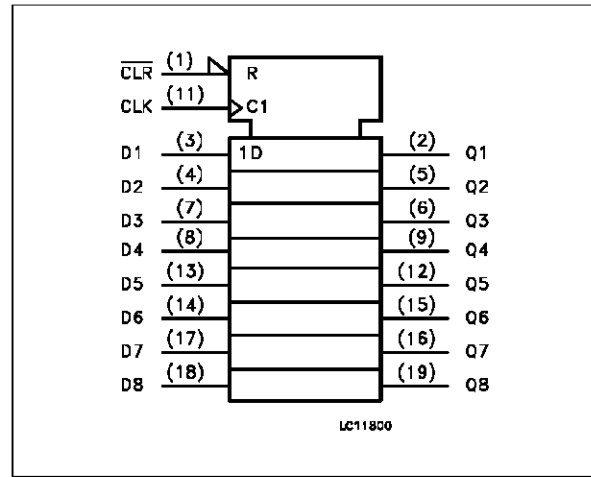
TRUTH TABLE

INPUTS			OUTPUS	FUNCTION
$\overline{\text{CLEAR}}$	CLOCK	D	Q	
L	X	X	L	CLEAR
H	⎍	L	L	
H	⎍	H	H	
H	⎁	X	Qn	NO CHANGE

X: Don't Care

LOGIC DIAGRAM
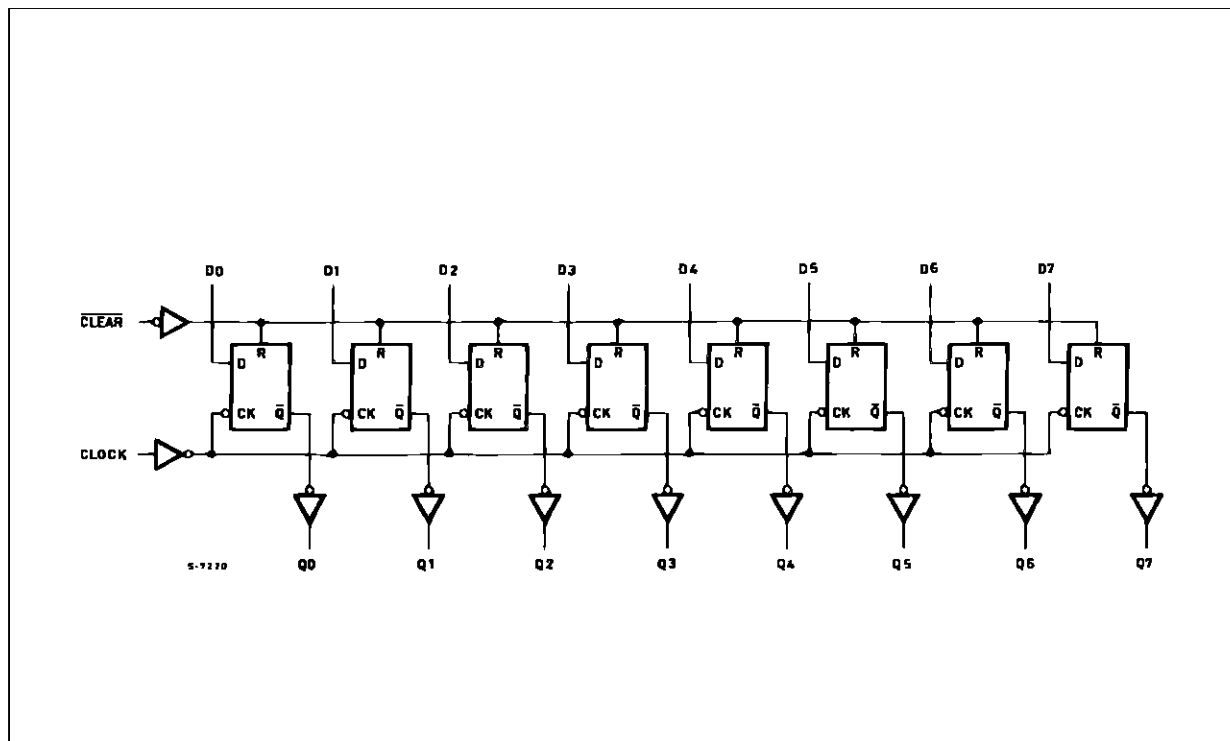
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	$\pm$ 20	mA
I_{OK}	DC Output Diode Current	$\pm$ 20	mA
I_O	DC Output Source Sink Current Per Output Pin	$\pm$ 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	$\pm$ 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	^{o}C
T_L	Lead Temperature (10 sec)	300	^{o}C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
(*) 500 mW: $\cong$ 65 ^{o}C derate to 300 mW by 10mW/^{o}C: 65 ^{o}C to 85 ^{o}C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature: **M54HC** Series		-55 to +125	^{o}C
	M74HC Series		-40 to +85	^{o}C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V	0 to 1000	ns
		V_{CC} = 4.5 V	0 to 500	
		V_{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

Symbol	Parameter	V_{CC} (V)	Test Conditions		T_A = 25 °C 54HC and 74HC Min.	Typ.	Max.	-40 to 85 °C 74HC Min.	Max.	-55 to 125 °C 54HC Min.	Max.	Unit
V_{IH}	High Level Input Voltage	2.0			1.5			1.5		1.5		V
		4.5			3.15			3.15		3.15		
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0					0.5		0.5		0.5	V
		4.5					1.35		1.35		1.35	
		6.0					1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	$V_I = V_{IH}$ or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I_O=-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I_O=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	$V_I = V_{IH}$ or V_{IL}	I_O= 20 µA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I_O= 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I_O= 5.2 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND				±0.1		±1		±1	µA
I_{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND				4		40		80	µA

SGS-THOMSON
MICROELECTRONICS

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

Symbol	Parameter	Test Conditions		Value							Unit
		V_{CC} (V)		T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0			25	75		95		110	ns
		4.5			7	15		19		22	
		6.0			6	13		16		19	
t_{PLH} t_{PHL}	Propagation Delay Time (CLOCK - Q)	2.0			54	145		180		220	ns
		4.5			18	29		36		44	
		6.0			15	25		31		37	
t_{PLH} t_{PHL}	Propagation Delay Time (CLEAR - Q)	2.0			60	160		200		240	ns
		4.5			20	32		40		48	
		6.0			17	27		34		41	
f_{MAX}	Maximum Clock Frequency	2.0		6	18		4.8		4		MHz
		4.5		30	56		24		20		
		6.0		35	66		28		24		
$t_{W(H)}$ $t_{W(L)}$	Minimum Pulse Width (CLOCK)	2.0			28	75		95		110	ns
		4.5			7	15		19		22	
		6.0			6	13		16		19	
$t_{W(L)}$	Minimum Pulse Width (CLEAR)	2.0			28	75		95		110	ns
		4.5			7	15		19		22	
		6.0			6	13		16		19	
t_s	Minimum Set-up Time	2.0			20	75		95		110	ns
		4.5			4	15		19		22	
		6.0			3	13		16		19	
t_h	Minimum Hold Time	2.0				0		0		0	ns
		4.5				0		0		0	
		6.0				0		0		0	
t_{REM}	Minimum Removal Time (CLEAR)	2.0			16	50		65		75	ns
		4.5			4	10		13		15	
		6.0			3	9		11		13	
C_{IN}	Input Capacitance				5	10		10		10	pF
C_{PD} (*)	Power Dissipation Capacitance				43						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/8$ (per Flip FLop), and the total CPD when n pcs of Flip Flop operate can be gained by the following equations: CPD (total) = 32 + 11 x n
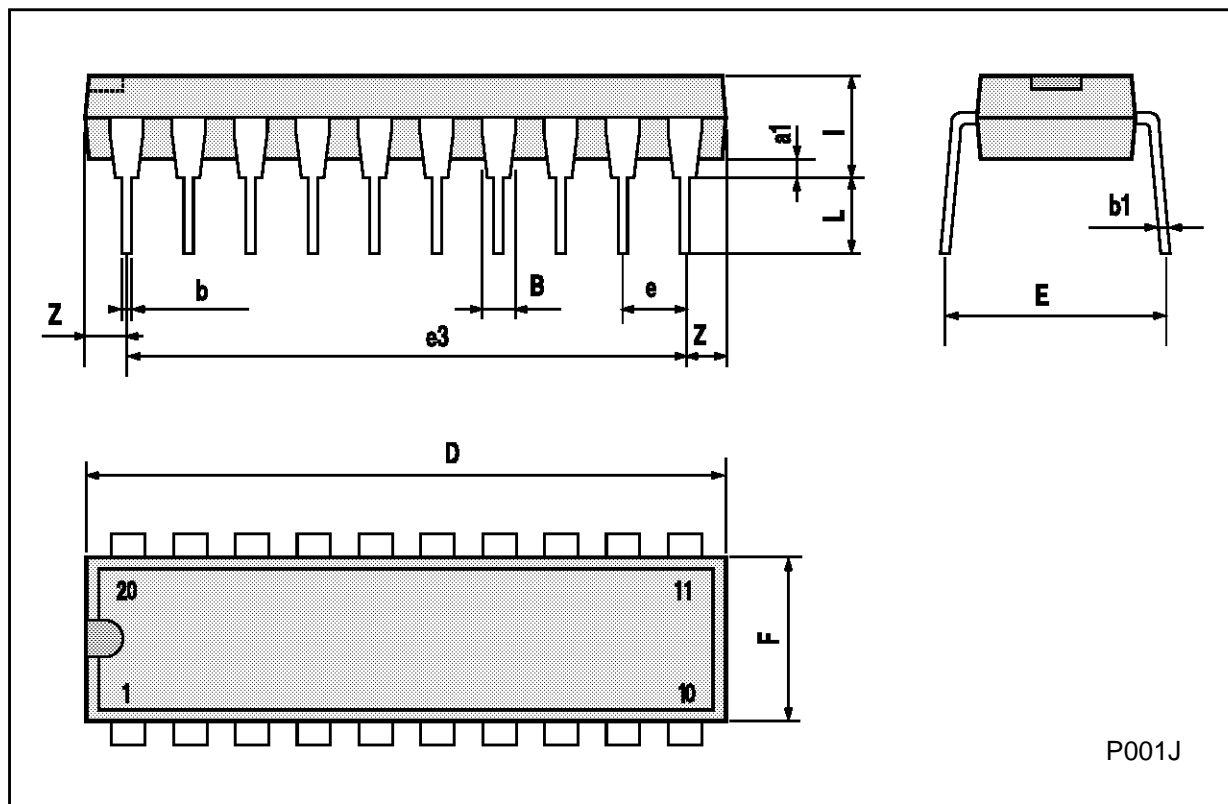
SWITCHING CHARACTERISTICS TEST WAVEFORM

$\overline{\text{CLEAR}}$ = "H"

DN = "H"

TEST CIRCUIT I_{CC} (Opr.)

SGS-THOMSON
MICROELECTRONICS
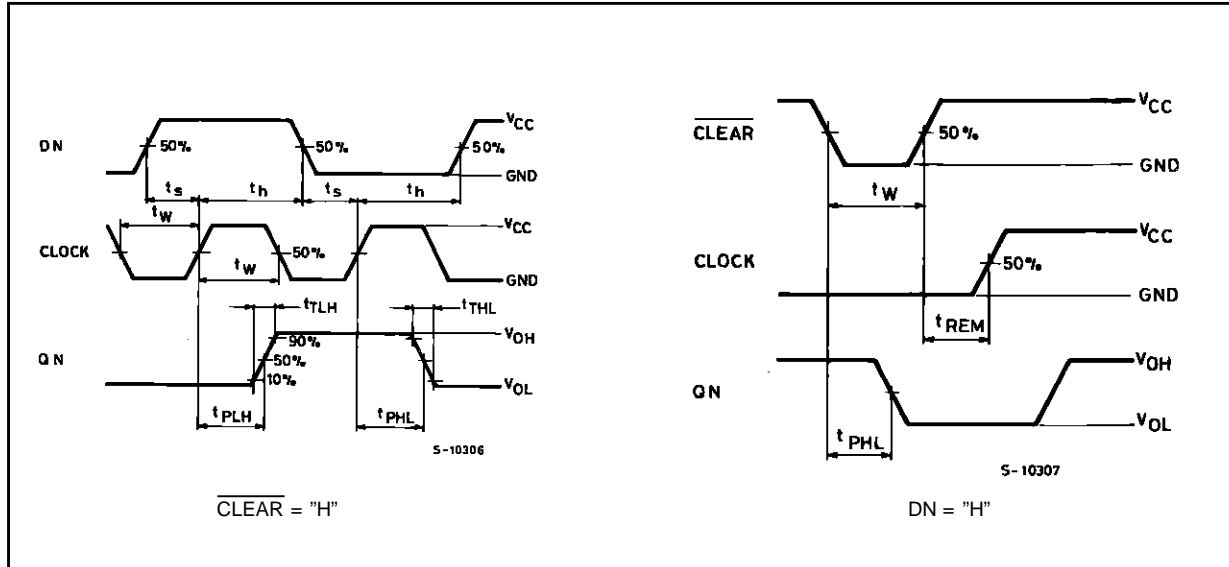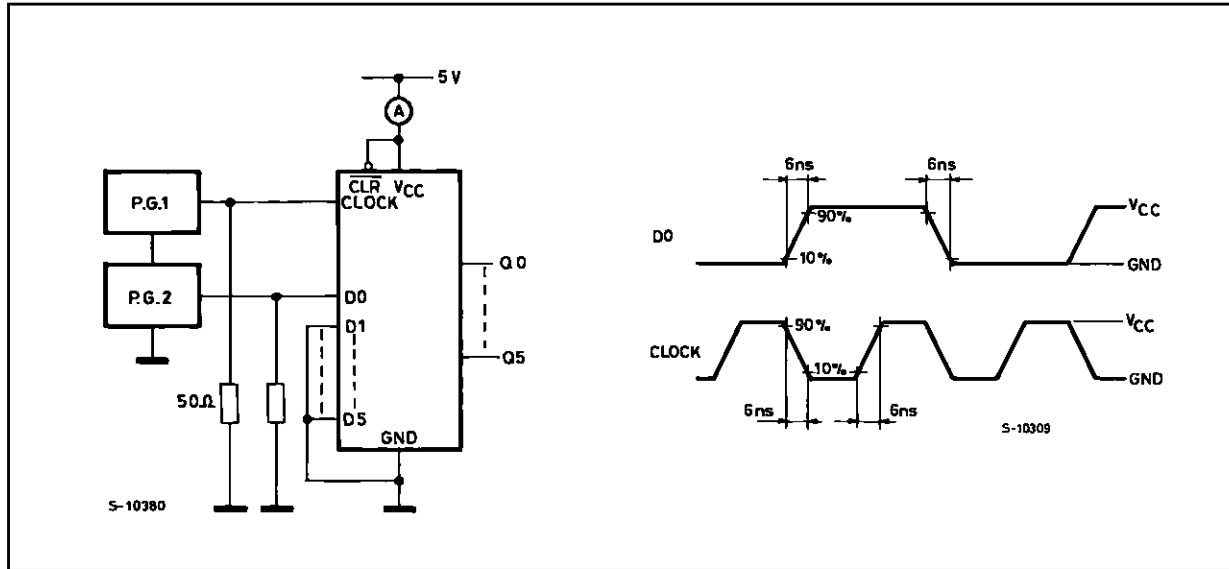
Plastic DIP20 (0.25) MECHANICAL DATA

DIM.	mm MIN.	mm TYP.	mm MAX.	inch MIN.	inch TYP.	inch MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053

P001J

SGS-THOMSON MICROELECTRONICS

Ceramic DIP20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			25			0.984
B			7.8			0.307
D		3.3			0.130	
E	0.5		1.78	0.020		0.070
e3		22.86			0.900	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
I	1.27		1.52	0.050		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N1	4° (min.), 15° (max.)					
P	7.9		8.13	0.311		0.320
Q			5.71			0.225

P057H

SGS-THOMSON
MICROELECTRONICS
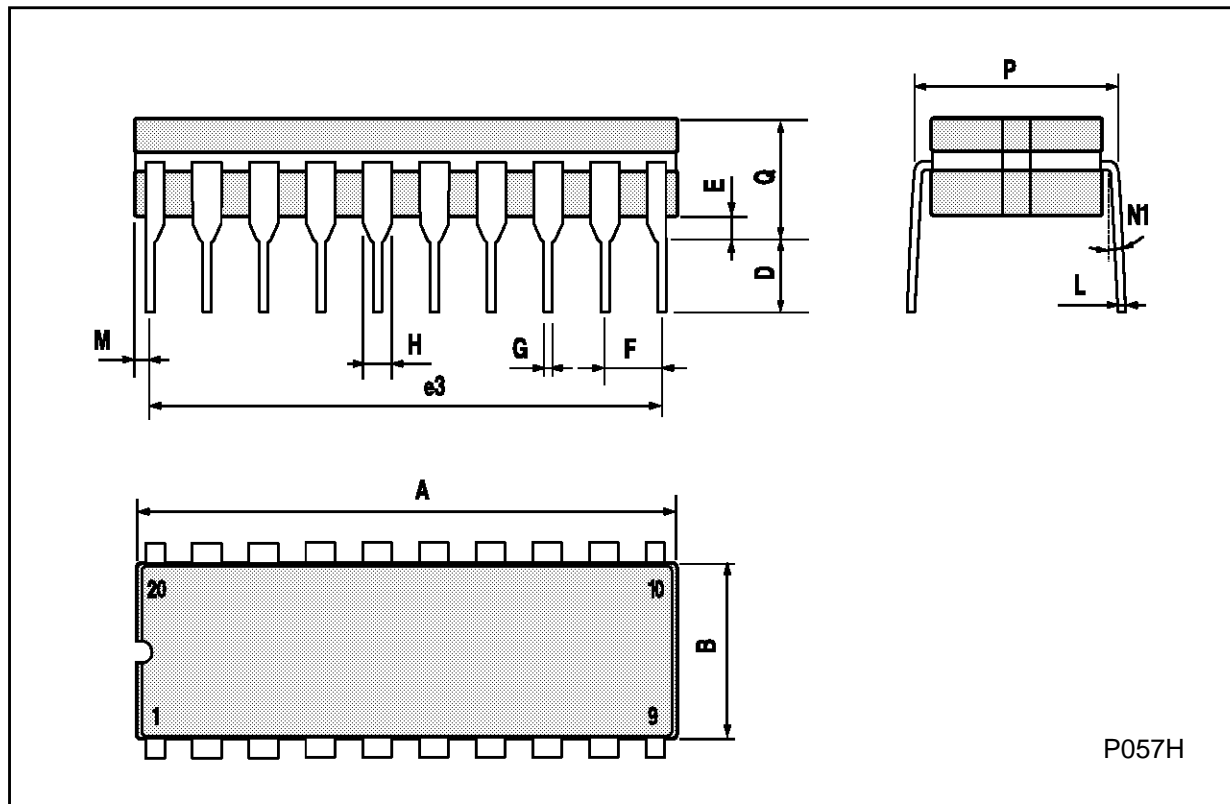
SO20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
M			0.75			0.029
S	8° (max.)					

P013L

SGS-THOMSON
MICROELECTRONICS
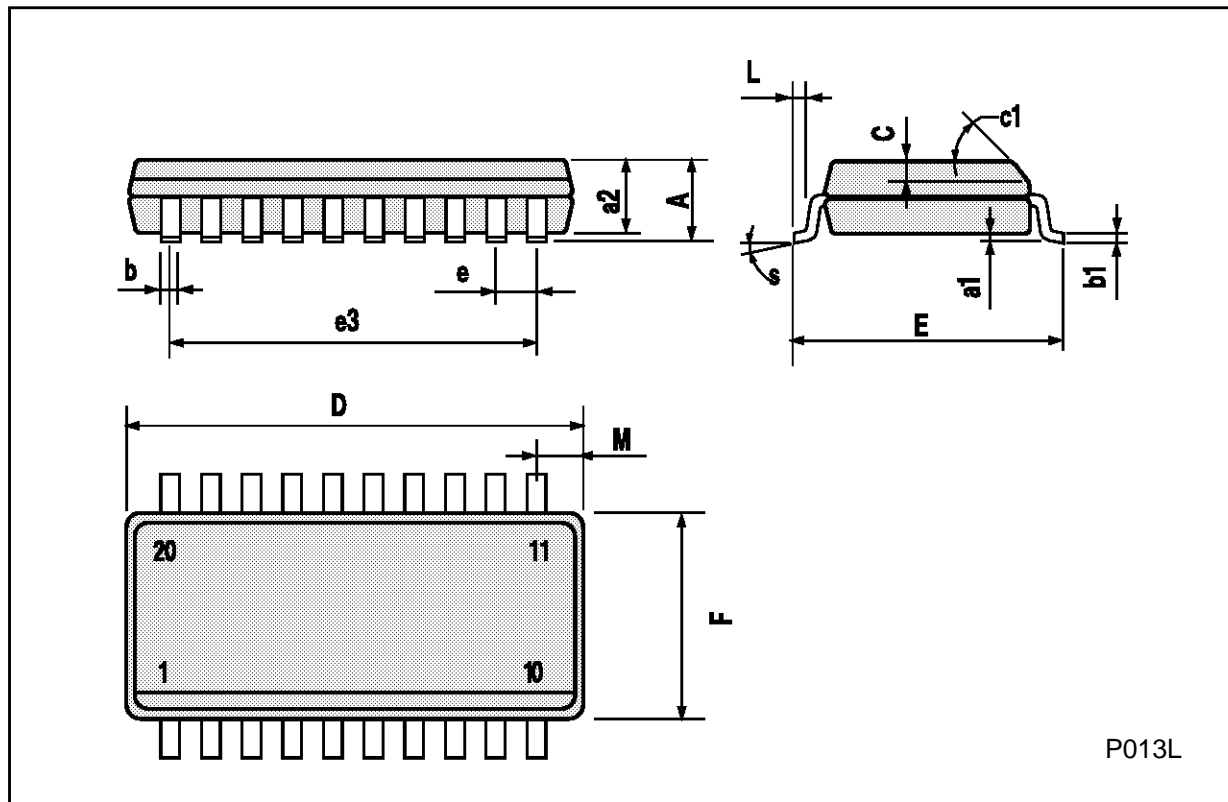
PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	**TYP.**	**MAX.**	**MIN.**	**TYP.**	**MAX.**
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	

G (Seating Plane Coplanarity)

P027A

SGS-THOMSON
MICROELECTRONICS